L Number	Hits	Search Text	DB	Time stamp
-	69	breakdown adj phenom\$4 NEAR5 dielectric	USPAT;	2004/03/02 13:55
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	1	"breakdown phenomena" near5 "ultra-thin dielectric layer"	USPAT;	2004/03/02 11:14
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	214	"breakdown phenomena"	USPAT;	2004/03/02 14:36
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	54	"ultra-thin dielectric layer"	USPAT;	2004/03/02 14:41
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	12	"breakdown phenomena" and " memory device"	USPAT;	2004/03/02 11:14
		broakdown priorioria and money across	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	4	(("6671040") or ("6667902")).PN.	USPAT:	2004/03/02 11:14
-	-	((557 1070) 61 (5501 502)).1 14.	US-PGPUB;	200-700/02 11.14
1			EPO; JPO;	
			DERWENT	
	14	BREAKDOWN ADJ PHENOMENA ADJ ULTRA-THIN ADJ	USPAT;	2004/03/02 11:14
-	14		US-PGPUB;	2004/03/02 11.14
		DIELECTRIC	EPO; JPO;	
			DERWENT	
	•	"20020063549"		2004/02/02 11:14
-	2	"20030063518"	USPAT; US-PGPUB;	2004/03/02 11:14
			EPO; JPO; DERWENT	
	60	(handledown or (handle adid down)) adi phonomed NEADE		2004/03/02 11:14
-	69	(breakdown or (breask adj1 down)) adj phenom\$4 NEAR5	USPAT;	2004/03/02 11:14
		dielectric	US-PGPUB;	
			EPO; JPO; DERWENT	
	-	"here ledouse above and "ultro this disloctric lover"	USPAT;	2004/03/02 11:59
-	. 7	"breakdown phenomena" and "ultra-thin dielectric layer"	· ·	2004/03/02 11.59
			US-PGPUB;	
			EPO; JPO;	
	0	(IIOZOO454II) DNI	DERWENT	2004/02/02 44:44
-	2	("6700151").PN.	USPAT;	2004/03/02 11:14
			US-PGPUB;	
			EPO; JPO;	
]	^	William this dialogue lover and breakdown ad whee	DERWENT	2004/03/02 11:14
-	9	"ultra-thin dielectric layer" and breakdown adj phenom\$9	USPAT;	2004/03/02 11:14
			US-PGPUB; EPO; JPO;	
]]			1 '	
	_	"brookdown phonomona" and "semicenductor more and	DERWENT USPAT;	2004/03/02 11:14
-	4	"breakdown phenomena" and "semiconductor memory	US-PGPUB;	2004/03/02 11:14
		device"		
			EPO; JPO;	
		Welling Alain with a state for really and Warrange and device W	DERWENT	2004/02/02 44:44
-	1	"ultra-thin dielectric layer" and " memory device"	USPAT;	2004/03/02 11:14
			US-PGPUB;	
			EPO; JPO;	
	_	((100740401) (100070001)) 551	DERWENT	0004/00/00 44 44
-	4	(("6671040") or ("6667902")).PN.	USPAT;	2004/03/02 11:14
			US-PGPUB;	
			EPO; JPO;	
	_		DERWENT	0004/55/55
-	2	"20040008538"	USPAT;	2004/03/02 11:59
j			US-PGPUB;	
			EPO; JPO;	
l			DERWENT	

	2	("6215140").PN.	USPAT;	2004/03/02 14:10
-	_	(0213140).FN.	US-PGPUB:	2004/03/02 14.10
			EPO; JPO;	
			DERWENT	
_	2	("4037243").PN.	USPAT;	2004/03/02 14:34
-	_	(4007240).1 14.	US-PGPUB;	2004/00/02 14:04
			EPO; JPO;	
			DERWENT	
_	31986	programmable adj1 read adj1only adj1 memory	USPAT;	2004/03/02 14:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	20955	programmable adj1 read adj1only adj1 memory	USPAT	2004/03/02 14:36
-	9	(programmable adj1 read adj1only adj1 memory) and	USPAT;	2004/03/02 14:52
		"breakdown phenomena"	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	31557	"programmable read only memory"	USPAT;	2004/03/02 14:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	20695	"programmable read only memory"	USPAT	2004/03/02 14:41
-	3	"programmable read only memory" and "ultra-thin dielectric	USPAT;	2004/03/02 14:41
	ļ	layer"	US-PGPUB;	
			EPO; JPO;	
	2	"20020074206"	DERWENT	2004/03/02 14:52
-		"20030071296"	USPAT; US-PGPUB;	2004/03/02 14:52
			EPO; JPO;	
			DERWENT	
_	4	"20030071296" or "20030071315"	USPAT;	2004/03/02 15:34
_	-	20000071200 01 20000071010	US-PGPUB;	2004/03/02 13:54
			EPO; JPO;	
			DERWENT	
_	2	("6700151").PN.	USPAT;	2004/03/02 15:34
	_		US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	6	("20030071296" or "20030071315") or (("6700151").PN.)	USPAT;	2004/05/03 06:37
	1		US-PGPUB;	
	İ		EPO; JPO;	
			DERWENT	
-	3	("6700151").PN.	USPAT;	2004/05/03 07:38
			US-PGPUB;	
			EPO; JPO;	
	1		DERWENT	